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Eğitim Bilgileri

Doktora, Saint-Petersburg State Technical University, Fizik, Rusya 1987 - 1991

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Lisans, Semerkant Devlet Üniversitesi, Fizik, Özbekistan 1975 - 1980

Biyografi

ÖZGEÇMİŞ VE ESERLER LİSTESİ

ÖZGEÇMİŞ

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Doğum Tarihi: 08 08 1958

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Derece	Bölüm/Program	Üniversite	Yıl
Lisans	Fizik	Semerkant Devlet Üniversitesi	1980
Y. Lisans	Yarıiletken Fiziği	İoffe Fizik Teknik Araştırma Enstitüsü (Sankt-Petersburg, Rusya)	1987
Doktora/S.Yeterlik/ Tıpta Uzmanlık	Yarıiletken Fiziği	İoffe Fizik Teknik Araştırma Enstitüsü (Sankt-Petersburg, Rusya)	1991

Yüksek Lisans Tez Başlığı (özeti ekte) ve Tez Danışman(lar)ı :

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Doctor of Science Mikhailova M.P.

Görevler:

Görev Unvanı	Görev Yeri	Yıl
Arş.Gör.	SSCB Bilimler Akademisi, İOFFE Fizik-Teknik Elektronlu Yarıiletkenler Laboratuvarı, Rusya	Araştırma Enst. St.Petersburg, 1985-1991
Öğr.Gör.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1991-1992
Yrd.Doç.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1992-1994
Doç.Dr.	Namangan Devlet Üniversitesi, Fizik Fakültesi,	Özbekistan 1994-1997
Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü yabancı uyruklu öğretim üyesi)	(sözleşmeli) 1997-2004
Yrd.Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2004-2006
Doç.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2006-2012
Prof.Dr.	Uludağ Üniversitesi, Fen-Ed. Fak., Fizik Bölümü	2012-

Yabancı Diller

Rusça, B2 Orta Üstü

Araştırma Alanları

Temel Bilimler

Akademik Unvanlar / Görevler

Prof. Dr., Bursa Uludağ Üniversitesi, FEN-EDEBİYAT FAKÜLTESİ, FİZİK, 2012 - Devam Ediyor

Doç. Dr., Bursa Uludağ Üniversitesi, FEN-EDEBİYAT FAKÜLTESİ, FİZİK, 2006 - Devam Ediyor

Yönetilen Tezler

AHMETOĞLU M., Elektrodepozisyon yoluyla elde edilmiş olan ni/n-gaas schottky diyotlarının elektriksel ve optik özelliklerinin incelenmesi, Yüksek Lisans, T.Batmaz(Öğrenci), 2020

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AHMETOĞLU M., Dar bantlı gainassb termofotovoltaiik yapıların elektrik ve optik özelliklerinin incelenmesi, Doktora, B.KUCUR(Öğrenci), 2017

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AHMETOĞLU M., N-GaSb/n-GalnAsSb/N-GaAlAsSb izotip heteroyapıların elektrik ve fotoelektrik özelliklerinin incelenmesi, Doktora, M.ÖZER(Öğrenci), 2005

SCI, SSCI ve AHCI İndekslerine Giren Dergilerde Yayınlanan Makaleler

- I. **Narrow-band n-GaN/n-Si isotype heterojunction photodiode: A simplified approach for photodiode development**
Olkun A., Kaplan H. K., Akay S. K., Ahmetoğlu M., Pat S., Erdogan N.
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- II. **A new prospect to measure the built-in potential for photodiodes**
HACİİSMAİLOĞLU M. C., AHMETOĞLU M.
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- III. **Electrical and optical properties of Schottky diodes fabricated by electrodeposition of Ni films on n-GaAs**
HACİİSMAİLOĞLU M. C., AHMETOĞLU M., ŞAFAK HACİİSMAİLOĞLU M., ALPER M., Batmaz T.
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- IV. **A novel self-powered filterless narrow-band near-infrared photodiode of Cu₂S/Si p(+)-p isotype heterojunction device with very low visible light noise**
Kaplan H. K., Akay S. K., Ahmetoğlu M.
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- V. **Photodiodes for Detecting the Emission of Quantum-Sized Disc Lasers Operating in the Whispering Gallery Modes (2.2-2.3 μ m)**
Kunitsyna E., Royz M. A., Andreev I. A., Grebenshchikova E. A., Pivovarova A. A., Ahmetoglu (Afrailov) M., Lebiadok Y., Mikulich R. Y., Iliinskaya N. D., Yakovlev Y. P.
SEMICONDUCTORS, cilt.54, ss.796-802, 2020 (SCI-Expanded)
- VI. **Electrical and optical properties of photodiode structures formed by surface polymerization of P(EGDMA-Vpca)-Swcnt films on n-si**

Kirezli B., Gucuyener İ., Kara A., Kaplan H. K., Afrailov M.

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- VII. **Electrical and optical properties of photodiode structures formed by surface polymerization of [P (EGDMA-VPCA)-SWCNT] films on n-GaAs**
Kirezli B., Ahmetoglu (Afrailov) M., Kara A.
JOURNAL OF MOLECULAR STRUCTURE, cilt.1192, ss.258-263, 2019 (SCI-Expanded)
- VIII. **N+-GaSb / no-GaInAsSb / P+-GaSb type ii heterojunction photodiodes with low radiation damage**
Ahmetoglu Afrailov M., Kirezli B., Kaynak G., Andreev I., Kunitsyna E., Mikhailova M., Yakovlev Y. P.
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- IX. **Photoelectrical properties of fabricated ZnS/Si heterojunction device using thermionic vacuum arc method**
Kaplan H. K., Akay S. K., Ahmetoglu M.
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- X. **N-GaSb / no-GaInAsSb / P- GaSb Type II Heterojunction Photodiodes with Low Radiation Damage**
Ahmetoğlu M., Kirazlı B., Kaynak G., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
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- XI. **The characteristics of ZnS/Si heterojunction diode fabricated by thermionic vacuum arc**
Kaplan H. K., Sarsici S., Akay S. K., Ahmetoglu M.
JOURNAL OF ALLOYS AND COMPOUNDS, cilt.724, ss.543-548, 2017 (SCI-Expanded)
- XII. **The electrical properties of Au/MEH-PPV:PCBM/n-type GaAs schottky barrier diode**
Ahmetoglu (Afrailov) M., Kirsoy A., Asimov A., Kucur B.
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- XIII. **Electrical Properties Inorganic-on-Organic Hybrid GaAs/Graphene Oxide Schottky Barrier Diode**
Ahmetoğlu M., Kirsoy A., Okutan M., Yakuphanoglu F.
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- XIV. **Poly(ethylene glycol dimethacrylate-co-1-vinyl-1,2,4-triazole/ carbon nanotube, single-walled)/n-GaAs Diode Formed by Surface Polymerization**
Ahmetoglu M., Kara A., Kucur B.
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- XV. **The Electrical Properties of Au/P3HT/n-Type Si Schottky Barrier Diode**
Asimov A., Ahmetoglu M., Kirsoy A., Ozer M., Yasin M.
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- XVI. **Electrical Characteristics and Temperature Dependence of Photovoltaic Parameters of GaInAsSb Based TPV Diode**
Kucur B., Ahmetoglu M., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
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- XVII. **The Electrical Properties of Au/P3HT/n-GaAs Schottky Barrier Diode**
Kirsoy A., Ahmetoglu (Afrailov) M., Asimov A., Kucur B.
ACTA PHYSICA POLONICA A, cilt.128, 2015 (SCI-Expanded)
- XVIII. **Electrical and Optical Characteristics of n-GaSb/n-GaIn_{0.24}AsSb/p-GaAl_{0.34}AsSb Heterostructure Photodiode**
Ahmetoglu M., Kucur B., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
ACTA PHYSICA POLONICA A, cilt.127, sa.4, ss.1007-1009, 2015 (SCI-Expanded)
- XIX. **Electrical Properties of GaInAsSb/GaSb/GaAlAsSb Double Heterostructure with Low Diameter**
Kucur B., Ahmetoglu M., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
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- XX. **Gaussian Distribution of inhomogeneous barrier height in Au/n-GaP (100) Schottky barrier diodes**
Ozer M., Guzel T., Asimov A., Ahmetoglu (Afrailov) M.
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- XXI. **The determination of electronic parameters of al/mdmo-ppv/p-si/al schottky diode by current-voltage characteristics**

- Asimov A., Ahmetoglu (Afrailov) M.
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- XXII. **Electrical characteristics of Al/n-type GaAs schottky barrier diodes at room temperature**
Asimov A., Ahmetoglu M., Kucur B., Gucuyener I.
Optoelectronics and Advanced Materials, Rapid Communications, cilt.8, ss.309-310, 2014 (SCI-Expanded)
- XXIII. **Determination of Carrier Concentrations in P-GaSb/n-InGaAsSb Type II Misaligned Heterojunctions by the Conductivity-Magnetic Field Dependence**
AHMETOĞLU M., Kucur B.
SENSOR LETTERS, cilt.11, sa.1, ss.202-204, 2013 (SCI-Expanded)
- XXIV. **The determination of series resistance and interface state density distributions of Au/p-type GaAs schottky barrier diodes**
Asimov A., Ahmetoglu (Afrailova) M., Kucur B., Ozer M., Guzel T.
Optoelectronics and Advanced Materials, Rapid Communications, cilt.7, ss.490-493, 2013 (SCI-Expanded)
- XXV. **Electrical properties of GaAs-GaAlAs near infrared light emitting diodes**
AHMETOĞLU M., Kucur B., GÜCÜYENER İ.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.6, ss.782-784, 2012 (SCI-Expanded)
- XXVI. **Photoelectrical characteristics of GaSb/GaInAsSb/GaAlAsSb heterojunction photodiodes under illumination by photons with wavelength of 0.95-1.0 μm**
Afrailov M.
THIN SOLID FILMS, cilt.520, sa.15, ss.5014-5017, 2012 (SCI-Expanded)
- XXVII. **Electrical and optical characteristics of the InAs/InAs_{0.7}Sb_{0.1}P_{0.2} single heterojunction photodiodes for the spectral range 1.6-3.5 μm**
Ahmetoglu (Afrailov) M., Andreev I. A., Kunitsyna E. V., Moiseev K. D., Mikhailova M. P., Yakovlev Y. P.
INFRARED PHYSICS & TECHNOLOGY, cilt.55, sa.1, ss.15-18, 2012 (SCI-Expanded)
- XXVIII. **The electrical characterization of electrodeposited Ni thin film on silicon: Schottky Barrier diodes**
AHMETOĞLU M., Tekgul A., ALPER M., Kucur B.
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- XXIX. **Electrical properties of Poly(ethylene glycol dimethacrylate-n-vinyl imidazole)/Single Walled Carbon Nanotubes/n-Si Schottky diodes formed by surface polymerization of Single Walled Carbon Nanotubes**
AHMETOĞLU M., KARA A., TEKİN N., Beyaz S., KÖÇKAR H.
THIN SOLID FILMS, cilt.520, sa.6, ss.2106-2109, 2012 (SCI-Expanded)
- XXX. **Narrow gap III-V materials for infrared photodiodes and thermophotovoltaic cells**
Kunitsyna E. V., Andreev I. A., Sherstnev V. V., L'vova T. V., Mikhailova M. P., Yakovlev Y. P., Ahmetoglu (Afrailov) M., Kaynak G., Gurler O.
OPTICAL MATERIALS, cilt.32, sa.12, ss.1573-1577, 2010 (SCI-Expanded)
- XXXI. **Electrical and optical properties of the GaInAsSb-based heterojunctions for infrared photodiode and thermophotovoltaic cell application**
Ahmetoglu (Afrailov) M., Kucur B., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
INFRARED PHYSICS & TECHNOLOGY, cilt.53, sa.5, ss.399-403, 2010 (SCI-Expanded)
- XXXII. **Dark currents in GaInAsSb based heterojunction photodiodes with a low diameter area at low temperatures**
Ahmetoglu (Afrailov) M.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.4, sa.4, ss.441-444, 2010 (SCI-Expanded)
- XXXIII. **Determination of the parameters for the back-to-back switched Schottky barrier structures**
Ahmetoglu M., Akay S. K.
CURRENT APPLIED PHYSICS, cilt.10, sa.2, ss.652-654, 2010 (SCI-Expanded)
- XXXIV. **Photoelectrical characteristics of the InAsSbP based uncooled photodiodes for the spectral range**

1.6-3.5 μm

Afrailov M.

INFRARED PHYSICS & TECHNOLOGY, cilt.53, sa.1, ss.29-32, 2010 (SCI-Expanded)

- XXXV. **Photoelectrical properties of InP-InGaAsP heterojunction avalanche photodiodes**
Ahmetoglu M., Ozer M., Kadirov O.
OPTOELECTRONICS AND ADVANCED MATERIALS-RAPID COMMUNICATIONS, cilt.3, sa.6, ss.608-611, 2009 (SCI-Expanded)
- XXXVI. **TO THE THEORY OF ELECTROMOTIVE FORCE GENERATED IN POTENTIAL BARRIER AT ULTRAHIGH FREQUENCY FIELD**
Ahmetoglu (Afrailov) M., Kaynak G., Shamirzaev S., Gulyamov G., Gulyamov A., Dadamirzaev M. G., Boydeda S. R., Aprailov N.
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- XXXVII. **Current transport in GaSb /GaInAsSb/GaAlAsSb heterojunction photodiodes**
Ahmetoglu (Afrailov) M.
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- XXXVIII. **Electron-hole interaction in spherical quantum dots of nanoheterostructures**
Ahmetoglu (Afrailov) M., Akay S. K., Boymatov P., Inoyatov S., Ahmedov O., Rahimov N., Pulatov A.
Optoelectronics and Advanced Materials, Rapid Communications, cilt.3, sa.3, ss.163-165, 2009 (SCI-Expanded)
- XXXIX. **Electrical Properties of Photodiodes Based on p-GaSb/p-GaInAsSb/N-GaAlAsSb Heterojunctions**
Ahmetoglu M., Kaynak G., Andreev I. A., Kunitsyna E. V., Mikhailova M. P., Yakovlev Y. P.
TECHNICAL PHYSICS LETTERS, cilt.34, sa.11, ss.937-940, 2008 (SCI-Expanded)
- XL. **Dark currents in GaSb/GaInAsSb heterojunction photodiodes at high temperatures**
Ahmetoglu (Afrailov) M.
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.10, sa.10, ss.2507-2510, 2008 (SCI-Expanded)
- XLI. **Photocurrent amplification in a isotype N+-GaSb/n(0)-GaInAsSb type II heterojunctions**
Ahmetoglu (Afrailov) M.
INFRARED PHYSICS & TECHNOLOGY, cilt.51, sa.6, ss.491-494, 2008 (SCI-Expanded)
- XLII. **Temperature dependence of electrical characteristics of Cr/p-Si(100) Schottky barrier diodes**
Erturk K., HACIİSMAİLOĞLU M. C., Bektore Y., Ahmetoglu M.
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.22, sa.14, ss.2309-2319, 2008 (SCI-Expanded)
- XLIII. **Temperature dependence of electrical characteristics of Cu/n-Si Shottky barrier diodes formed by electrodeposition**
Ahmetoglu M., Erturk K.
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.10, sa.2, ss.298-301, 2008 (SCI-Expanded)
- XLIV. **Photoelectrical characteristic of isotype N+-GaSb / no-GaInAsSb / N+- GaAlAsSb type II heterojunctions**
AHMETOĞLU M., ÖZER M. H., Kadirov O., Boydedayev S.
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- XLV. **Electrical transport at a isotype type II heterojunctions in the system of GaSb-GaInAsSb**
Ahmetoglu (Afrailov) M.
THIN SOLID FILMS, cilt.516, sa.6, ss.1227-1231, 2008 (SCI-Expanded)
- XLVI. **Dark currents in the uncooled InAs/InAsSbP photodiodes for the spectral range 1.6-3.5 μm**
Ahmetoglu M.
JOURNAL OF OPTOELECTRONICS AND ADVANCED MATERIALS, cilt.9, sa.11, ss.3567-3570, 2007 (SCI-Expanded)
- XLVII. **Electrical properties of n-Si/Cu Schottky diodes formed by electrodeposition**
Ahmetoglu (Afrailov) M., Alper M., Safak M., Erturk K., Gurpinar B., Kocak F., Hacıismailoglu C.
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- XLVIII. **Avalanche photodiodes for electromagnetic calorimeters**
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NUCLEAR INSTRUMENTS & METHODS IN PHYSICS RESEARCH SECTION A-ACCELERATORS SPECTROMETERS

- DETECTORS AND ASSOCIATED EQUIPMENT, sa.1, ss.120-121, 2007 (SCI-Expanded)
- XLIX. **Electrical properties of isotype N+-GaSb/n(0)-GaInAsSb/N+-GaAlAsSb type-II heterojunctions**
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- L. **Change in the resistance of the semiconductor in the variable deformation field**
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- LI. **Dark currents in the uncooled InAs / InAsSbP photodiodes for the spectral range 1.6 - 3.5 μm**
AHMETOĞLU M.
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- LII. **Electrical properties of n-Si /Cu Schottky diodes formed by electrodeposition**
AHMETOĞLU M., ALPER M., Safak M., Erturk K., Gurpinar B., KOÇAK F., HACIİSMAİLOĞLU M. C.
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- LIII. **A ZnS-Si isotype heterojunction avalanche photodiode structure for scintillation light detection**
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- LIV. **Dark currents and impact ionization coefficients in the InP-InGaAsP double heterostructures**
Ozer M., Ahmetoglu M., Aprailov N.
INTERNATIONAL JOURNAL OF MODERN PHYSICS B, cilt.20, sa.29, ss.4929-4936, 2006 (SCI-Expanded)
- LV. **Electrical and photoelectrical properties of isotype N+-GaSb/n(0)-GaInAsSb type II heterojunctions**
Afrailov M.
INFRARED PHYSICS & TECHNOLOGY, cilt.45, sa.3, ss.169-175, 2004 (SCI-Expanded)
- LVI. **Optical Moisture Meter Based on GaInAsSb Led's and Photodiodes**
Akay C., Ahmetoğlu M., Özer M.
Romanian Journal Of Physics, cilt.49, sa.34, ss.251-256, 2004 (SCI-Expanded)
- LVII. **A ZnS-Si hetero-junction photodiode for short wavelength photon detection**
Tapan İ., Afrailov M.
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- LVIII. **Type II GaSb based photodiodes operating in spectral range 1.5-4.8 μm at room temperature**
Mikhailova M., Stoyanov N., Andreychuk O., Moiseev K., Andreev I., Yakovlev Y., Afrailov M.
IEE PROCEEDINGS-OPTOELECTRONICS, cilt.149, sa.1, ss.41-44, 2002 (SCI-Expanded)
- LIX. **Photodiodes for a 1.5-4.8 μm spectral range based on type-II GaSb/InGaAsSb heterostructures**
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- LX. **Temperature Dependence of Photo VAC of Vidicon Target on the Base of a-Si:H**
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- LXI. **Determination of the values of band-edge discontinuities ΔE_v and ΔE_c at the heterojunction of N-GaSb/n-GaInAsSb isotype structures by photovoltaic method**
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